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PATENT DATE

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	APPLICATION NO. 09/942445	CONT/PRIOR F	CLASS 438	SUBCLASS	ART UNIT 2812	Ber Cary	j., 3

Toshimichi Kurihara Takashi Ueda

ISSUE CLASSIFICAT

JC 1061

Semiconductor device and manufacturing method thereof

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		ISSUING C	LASSIFICATION
ORIGIN	AL		CROSS REFERENCE(S)
CLASS SUBCLASS		CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)
INTERNATIONA	L CLASSIFICATION		
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TERMINAL		DRAWINGS		CLAIMS ALLOWED		
DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
				NOTICE OF ALLOWANCE MAILED		
The term of this patent subsequent to (date) has been disclaimed.	(Assistant Examiner) (Date)			•	· ·	
The term of this patent shall				•		
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this patent have been disclaimed.	(Legal instruments Examiner) (Date)		(Date)			
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